

### **ABSTRACT OF THE DISCLOSURE**

The present invention relates to a method of forming metal wiring in a semiconductor device, and the method includes forming a bottom metal pattern on a semiconductor substrate, forming an insulating layer on the semiconductor substrate including the bottom metal pattern, forming a first photoresist pattern for forming via hole on the insulating layer, forming an unfinished via hole by removing the insulating layer selectively for a prescribed thickness using the first photoresist pattern as a mask, removing the first photoresist pattern, forming a second photoresist pattern for forming damascene pattern on the insulating layer around the unfinished via hole, forming a damascene pattern by removing the insulating layer selectively using the second photoresist pattern as a mask, removing the second photoresist pattern, and forming a metal wiring via damascene contact by filling metal in the damascene pattern. According to the present invention, semiconductor manufacturing yield is improved by preventing via hole defects during dual damascene process.